3. The semiconductor device according to claim 1, wherein said ring-shaped conductive layer is formed of a same material as said gate electrodes of said MOS transistors.

4. The semiconductor device according to claim 1, wherein said bipolar transistor comprises an insulation film that provides insulation between said emitter electrode and a base region only within said ring-shaped conductive layer.

5. The semiconductor device according to claim 1, wherein an insulation film that forms said side walls of said MOS transistors and an insulation film that provides insulation between said emitter electrode and a base region are formed of different insulation films.

6. The semiconductor device according to claim 1, wherein a variation of a drain current of said MOS transistors is between 1 and 5 percent.

7. The semiconductor device according to claim 1, wherein said emitter electrode has an outer periphery part which is formed over said ring-shaped conductive layer.

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